

## WHAT IS CLAIMED IS:

1. A method for burning in a wafer having an insulator layer formed on one surface and a plurality of active device, each device having a first and second electrode, comprising:

5 forming a conductive interconnect layer adjacent said insulator layer, wherein said conductive interconnect layer electrically couples together at least the first electrode of at least a portion of the active devices.

10 2. The method of claim 1 further comprising coupling said wafer to a test apparatus, coupling at least one test probe to said conductive interconnect layer and simultaneously applying a predetermined power to each of the active devices in said portion of the active devices.

15 3. The method of claim 2 wherein applying a predetermined power to each of the active devices in the said portion of the active devices comprises driving each of the active devices in the said portion of the active devices with a substantially uniform current or voltage.

20 4. The method of claim 1 further comprising processing said conductive interconnect layer to form one or more common contact traces, wherein said one or more common contact traces electrically couple together at least the first electrode of said portion of the active devices.

25 5. The method of claim 4 further comprising forming a resistor between said one or more common contact traces and the first electrode of said portion of the active devices.

6. The method of claim 5 wherein forming a resistor between said one or more common contact traces and the first electrode of said portion of the active devices comprises processing said conductive interconnect layer between said one or more common contact traces and the first electrode of said portion of the active devices.

7. The method of claim 5 wherein processing said conductive interconnect layer comprises forming a serpentine pattern in the conductive interconnect layer between said one or more common contact traces and the first electrode of said portion of the active devices.

8. The method of claim 5 wherein forming a resistor between said one or more common contact traces and the first electrode of said portion of the active devices comprises forming a resistive bridge between said one or more common contact traces and the first electrode of said portion of the active devices.

9. The method of claim 5 further comprising coupling said wafer to a test apparatus, coupling at least one test probe to said conductive interconnect layer and simultaneously applying a predetermined power to each of the active devices in said portion of the active devices.

10. The method of claim 4 further comprising forming a fuse between said one or more common contact traces and the first electrode of said portion of the active devices.

11. The method of claim 10 further comprising probing said active devices and blowing fuse associated with failed active devices.

5 12. The method of claim 11 further comprising coupling said wafer to a test apparatus, coupling at least one test probe to said conductive interconnect layer and simultaneously applying a predetermined power to each of the active devices in said portion of the active devices.

10 13. The method of claim 12 further comprising removing said insulator layer and said conductive interconnect layer.

15 14. The method of claim 1 wherein forming a conductive interconnect layer adjacent said insulator layer comprises coupling said wafer to a conductive liquid within a test apparatus, wherein said conductive liquid electrically couples together at least the first electrode of at least a portion of the active devices.

20 15. The method of claim 14 further comprising removing said insulator layer and said conductive interconnect layer.

25 16. A method for burning in a wafer having an insulator layer formed on one surface and a plurality of active device, each device having a first and second electrode, comprising:  
forming a first conductive interconnect layer adjacent said insulator layer;  
processing said conductive interconnect layer to one or  
30 more first electrode contact traces wherein each of said first electrode common contact traces separately couples together the first electrode of each active device within an array; and

processing said first conductive interconnect layer to form one or more second electrode common contact traces wherein said second electrode contact traces simultaneously couple together the second electrode of at least a portion of said active devices.

17. The method of claim 16 further comprising coupling a first test probe to at least a portion of said first electrode common contact traces, coupling a second test probe to at least a portion of said second electrode common contact traces and simultaneously applying a predetermined current or voltage across said first and second test probes.

18. The method of claim 17 further comprising removing said insulator layer and said conductive interconnect layer.

19. The method of claim 16 further comprising forming a resistor between said one or more first electrode common contact traces and the first electrode of said active devices.

20. The method of claim 19 wherein forming a resistor between said one or more first electrode common contact traces and the first electrode of said active devices comprises processing said first conductive interconnect layer between said one or more first electrode common contact traces and the first electrode of said portion of the active devices.

21. The method of claim 19 wherein processing said first conductive interconnect layer comprises forming a serpentine pattern in the first conductive interconnect layer between said one or more first electrode common contact traces and the first electrode of said active devices.

22. The method of claim 16 further comprising depositing a second insulator layer adjacent said first conductive interconnect layer, forming a first contact adjacent to a first portion of said second insulator layer that simultaneously couples together at least a portion of the first electrode common contact traces of at least a portion of the active devices, forming a second contact adjacent a second portion of said second insulator layer that simultaneously couples together at least a portion of said second electrode common contact traces.

23. The method of claim 22 further comprising coupling a first test probe to said first contact, coupling a second test probe to said second contact and simultaneously applying a predetermined voltage across said contacts.

24. The method of claim 23 further comprising removing said first and second insulator layers, said first conductive interconnect layer and said first and second contacts.

25. The method of claim 22 further comprising forming a resistor between said first contact at least said portion of said first electrode common contact traces.

26. The method of claim 22 further comprising forming a fuse between said first contact at least said portion of said first electrode common contact traces.

27. The method of claim 26 further comprising probing said active devices and blowing fuse associated with failed active devices.

28. The method of claim 27 further comprising coupling a first test probe to said first contact, coupling a second test probe to said second contact and simultaneously applying a  
5 predetermined current or voltage across said contacts.

29. The method of claim 28 further comprising removing said first and second insulator layers, said first conductive interconnect layer and said first and second contacts.

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